

Silicon Carbide (SiC) MOSFET - EliteSiC, 16 mohm 650 V, M3S, TO247-4L, THIN LEADS NTH4LN016N065M3S

Features

- Typical $R_{DS(on)} = 16 \text{ m}\Omega @ V_{GS} = 18 \text{ V}$
- Ultra Low Gate Charge ($Q_{G(tot)} = 100 \text{ nC}$)
- High Speed Switching with Low Capacitance ($C_{oss} = 208 \text{ pF}$)
- 100% Avalanche Tested
- This Device is Halide Free and RoHS Compliant with Exemption 7a, Pb-Free 2LI (on second level interconnection)

Applications

- SMPS, Solar Inverters, UPS, Energy Storage, EV Charging Infrastructure

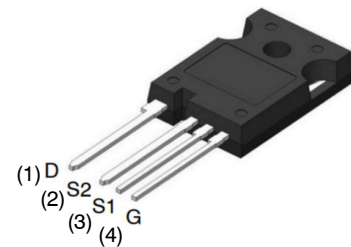
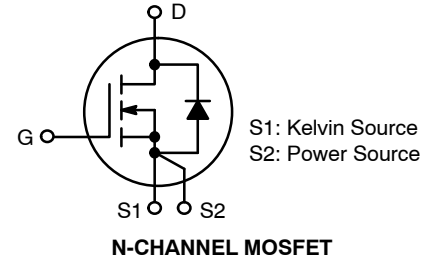
MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	650	V
Gate-to-Source Voltage	V_{GS}	-10/+22.6	V
Gate-to-Source Transient Voltage	$t_p < 0.5 \mu\text{s}$, Duty cycle $\leq 1\%$	V_{GS} -11 / +25	V
Continuous Drain Current	$T_C = 25^\circ\text{C}$	I_D 71	A
Power Dissipation		P_D 300	W
Continuous Drain Current	$T_C = 100^\circ\text{C}$	I_D 50	A
Power Dissipation		P_D 150	W
Pulsed Drain Current (Note 1)	$T_C = 25^\circ\text{C}$ $t_p = 100 \mu\text{s}$	I_{DM} 243	A
Continuous Source-Drain Current (Body Diode)	$T_C = 25^\circ\text{C}$ $V_{GS} = -3 \text{ V}$	I_S 48	A
	$T_C = 100^\circ\text{C}$ $V_{GS} = -3 \text{ V}$	28	
Pulsed Source-Drain Current (Body Diode) (Note 1)	$T_C = 25^\circ\text{C}$ $V_{GS} = -3 \text{ V}$, $t_p = 100 \mu\text{s}$	I_{SM} 226	
Single Pulse Avalanche Energy (Note 2)	$I_{LPK} = 60 \text{ A}$, $L = 0.1 \text{ mH}$	E_{AS} 180	mJ
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +175	$^\circ\text{C}$
Lead Temperature for Soldering Purposes (1/8" from case for 10 seconds)	T_L	270	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Single pulse, limited by max junction temperature.
2. E_{AS} of 180 mJ is based on starting $T_J = 25^\circ\text{C}$, $L = 0.1 \text{ mH}$, $I_{AS} = 60 \text{ A}$, $V_{DD} = 100 \text{ V}$, $V_{GS} = 18 \text{ V}$.

$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D MAX
650 V	16 m $\Omega @ V_{GS} = 18 \text{ V}$	71 A



TO247-4L, THIN LEADS
CASE 340CW

MARKING DIAGRAM



4LN016065M3S = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping
NTH4LN016N065M3S	TO247-4L, Thin Leads	30 Units / Tube

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Note 3)	$R_{\theta JC}$	0.50	$^{\circ}\text{C/W}$

3. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Value	Unit
Operation Values of Gate-to-Source Voltage	V_{GSop}	-5...0 +18	V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

* Operation at 0 V turn-off requires consideration of switching behavior and system-level design trade-offs. Design guidance and application considerations are provided in Application Note [AND90255/D](#).

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}, T_J = 25^{\circ}\text{C}$	650			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 650\text{ V}, T_J = 25^{\circ}\text{C}$			10	μA
		$V_{DS} = 650\text{ V}, T_J = 175^{\circ}\text{C}$ (Note 5)			500	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = -10\text{ V}, V_{DS} = 0\text{ V}$	-1			μA
		$V_{GS} = +22.6\text{ V}, V_{DS} = 0\text{ V}$			1	

ON CHARACTERISTICS

Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 18\text{ V}, I_D = 30\text{ A}, T_J = 25^{\circ}\text{C}$		16	23.5	$\text{m}\Omega$
		$V_{GS} = 18\text{ V}, I_D = 30\text{ A}, T_J = 175^{\circ}\text{C}$ (Note 5)		25		
		$V_{GS} = 15\text{ V}, I_D = 30\text{ A}, T_J = 25^{\circ}\text{C}$		21		
		$V_{GS} = 15\text{ V}, I_D = 30\text{ A}, T_J = 175^{\circ}\text{C}$ (Note 5)		27		
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 15\text{ mA}, T_J = 25^{\circ}\text{C}$	2.0	2.7	4.0	V
Forward Transconductance	g_{FS}	$V_{DS} = 10\text{ V}, I_D = 30\text{ A}$ (Note 5)		27		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ (Note 5)		2735		pF
Output Capacitance	C_{OSS}			208		
Reverse Transfer Capacitance	C_{RSS}			18		
Total Gate Charge	$Q_{G(TOT)}$	$V_{DD} = 400\text{ V}, I_D = 30\text{ A}, V_{GS} = -3/18\text{ V}$ (Note 5)		100		nC
Gate-to-Source Charge	Q_{GS}			33		
Gate-to-Drain Charge	Q_{GD}			25		
Gate Resistance	R_G	$f = 1\text{ MHz}$		3.0		Ω

SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -3/18\text{ V}, V_{DD} = 400\text{ V}, I_D = 30\text{ A}, R_G = 4.7\text{ }\Omega, T_J = 25^{\circ}\text{C}$ (Notes 4, 5)		6.5		ns
Turn-Off Delay Time	$t_{d(OFF)}$			45		
Rise Time	t_r			20		
Fall Time	t_f			45		
Turn-On Switching Loss	E_{ON}			103		μJ
Turn-Off Switching Loss	E_{OFF}			100		
Total Switching Loss	E_{TOT}			203		

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ELECTRICAL CHARACTERISTICS ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified) (continued)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -3/18\text{ V}$, $V_{DD} = 400\text{ V}$, $I_D = 30\text{ A}$, $R_G = 4.7\text{ }\Omega$, $T_J = 175\text{ }^{\circ}\text{C}$ (Notes 4, 5)		4.7		ns
Turn-Off Delay Time	$t_{d(OFF)}$			55		
Rise Time	t_r			20		
Fall Time	t_f			13		
Turn-On Switching Loss	E_{ON}			104		μJ
Turn-Off Switching Loss	E_{OFF}			108		
Total Switching Loss	E_{TOT}			212		

SOURCE-TO-DRAIN DIODE CHARACTERISTICS

Continuous Source-Drain Diode Forward Current	I_{SD}	$V_{GS} = -3\text{ V}$, $T_C = 25\text{ }^{\circ}\text{C}$ (Note 5)			48	A
Pulsed Source-Drain Diode Forward Current (Note 1)	I_{SDM}				226	
Forward Diode Voltage	V_{SD}	$I_{SD} = 30\text{ A}$, $V_{GS} = -3\text{ V}$, $T_J = 25\text{ }^{\circ}\text{C}$		4.6		V
		$I_{SD} = 30\text{ A}$, $V_{GS} = -3\text{ V}$, $T_J = 175\text{ }^{\circ}\text{C}$ (Note 5)		4.3		
Reverse Recovery Time	t_{RR}	$V_{GS} = -3\text{ V}$, $I_S = 30\text{ A}$, $di/dt = 1000\text{ A}/\mu\text{s}$, $V_{DS} = 400\text{ V}$, $T_J = 25\text{ }^{\circ}\text{C}$ (Note 5)		23		ns
Charge Time	t_a			13		
Discharge Time	t_b			10		
Reverse Recovery Charge	Q_{RR}			146		nC
Reverse Recovery Energy	E_{REC}			12		μJ
Peak Reverse Recovery Current	I_{RRM}			11		A

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. E_{ON}/E_{OFF} result is with body diode.

5. Defined by design, not subject to production test.

TYPICAL CHARACTERISTICS

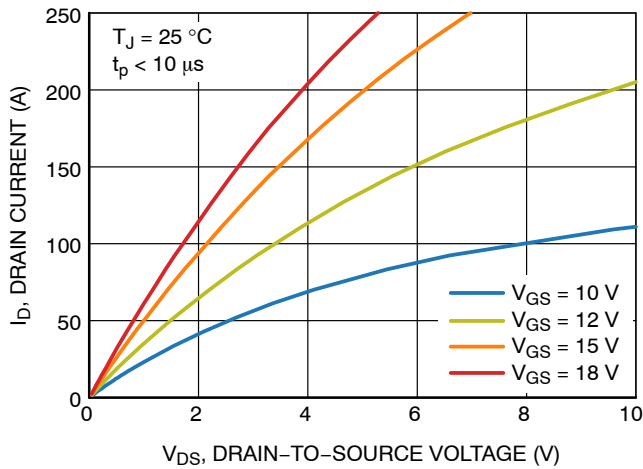


Figure 1. Output Characteristics

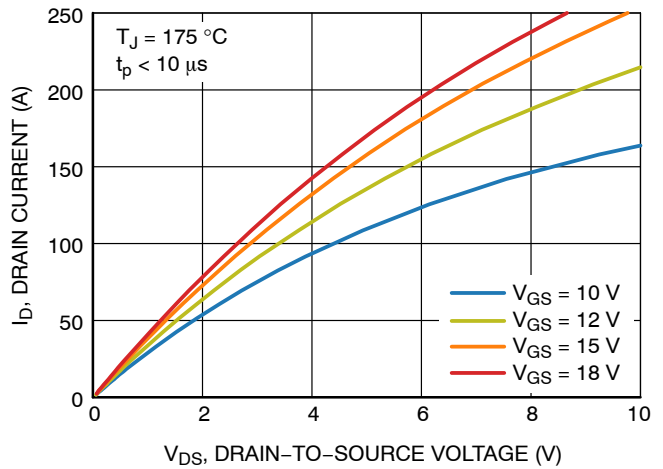


Figure 2. Output Characteristics

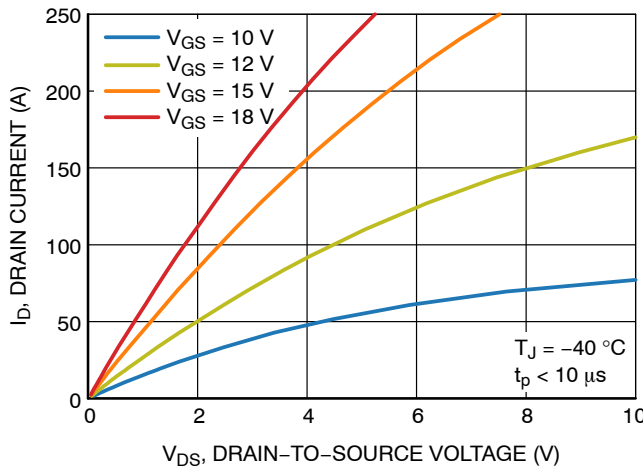


Figure 3. Output Characteristics

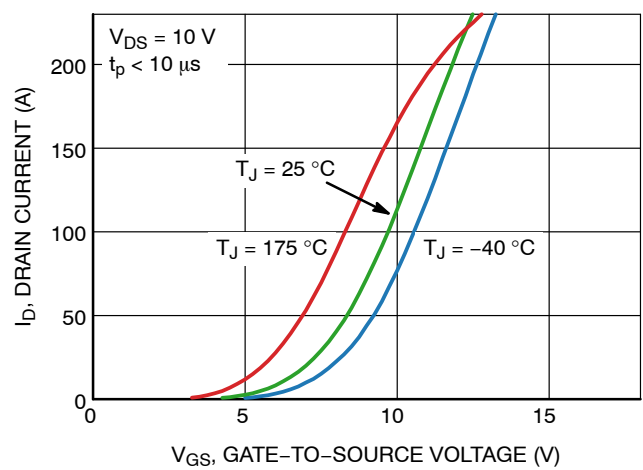


Figure 4. I_D vs. V_{GS}

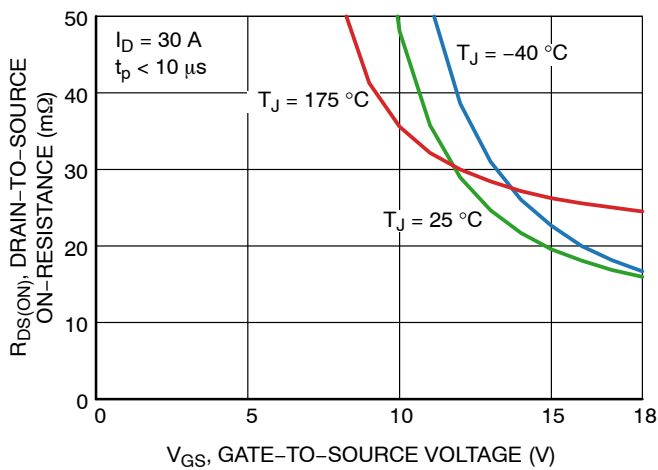


Figure 5. $R_{DS(ON)}$ vs. V_{GS}

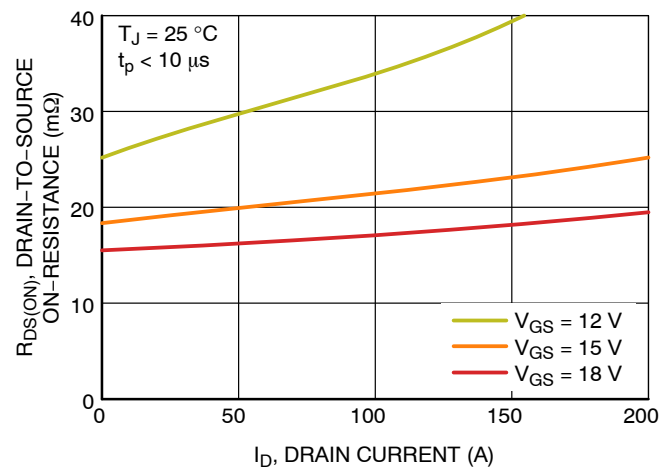


Figure 6. $R_{DS(ON)}$ vs. I_D

TYPICAL CHARACTERISTICS

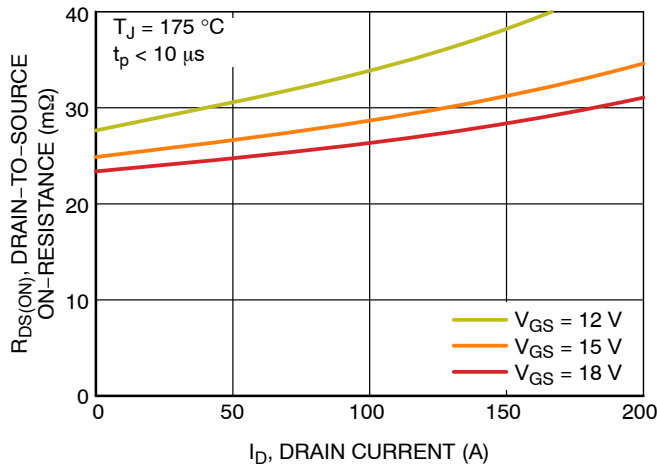


Figure 7. $R_{DS(ON)}$ vs. I_D

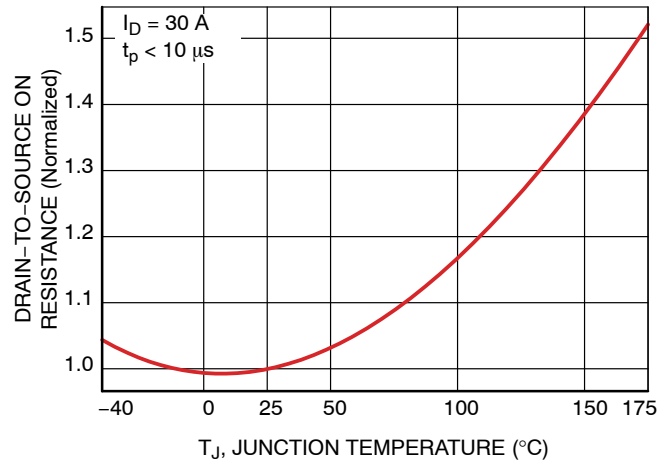


Figure 8. $R_{DS(ON)}$ vs. T_J

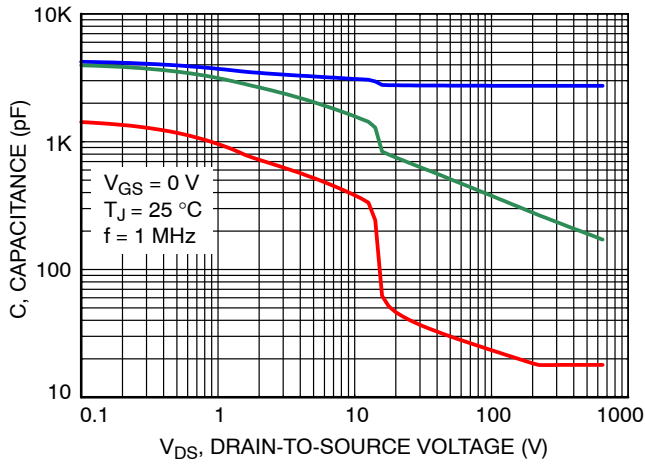


Figure 9. Capacitance Characteristics

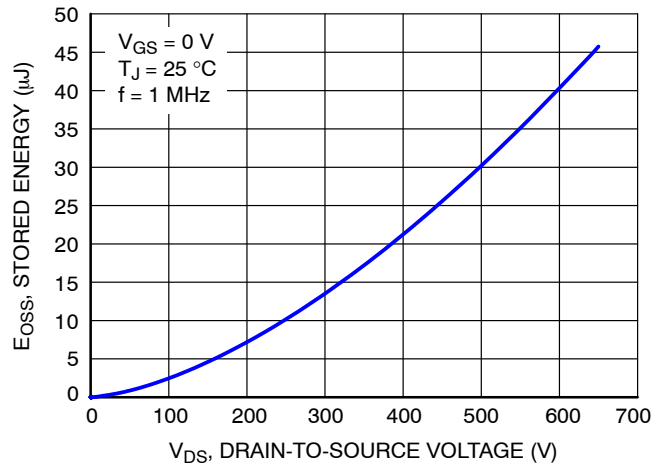


Figure 10. Stored Energy vs. Drain-to-Source Voltage

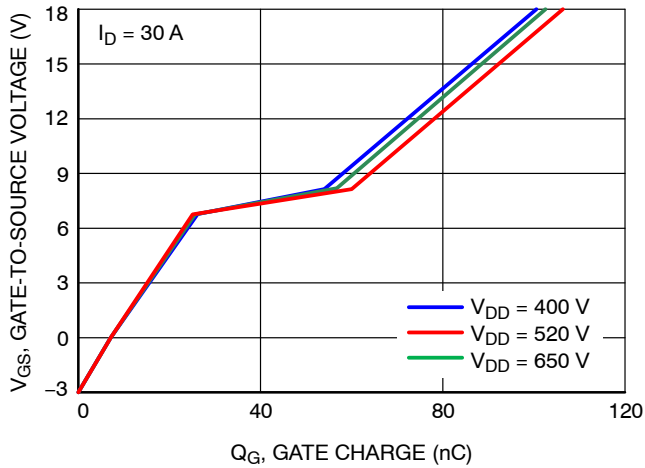


Figure 11. Gate Charge Characteristics

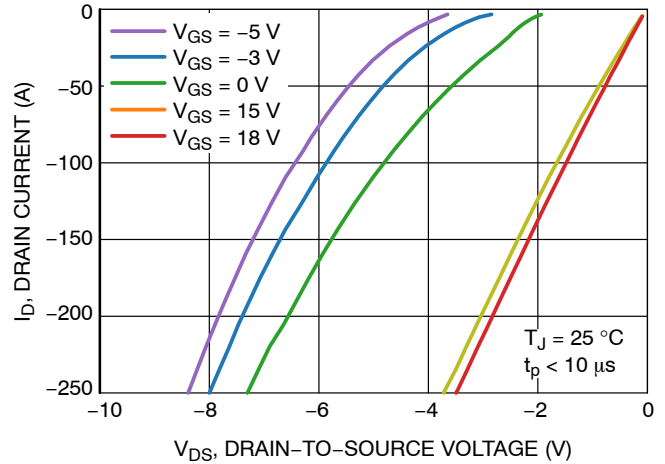


Figure 12. Reverse Conduction Characteristics

TYPICAL CHARACTERISTICS

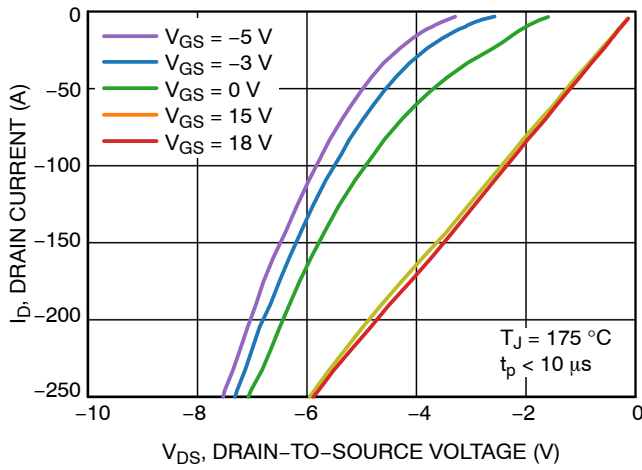


Figure 13. Reverse Conduction Characteristics

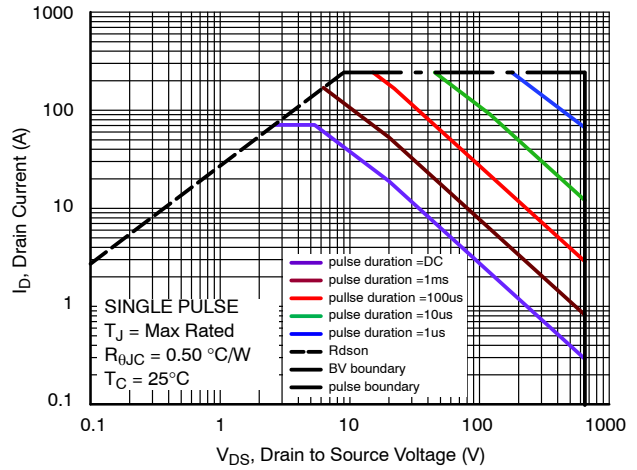


Figure 14. Safe Operating Area

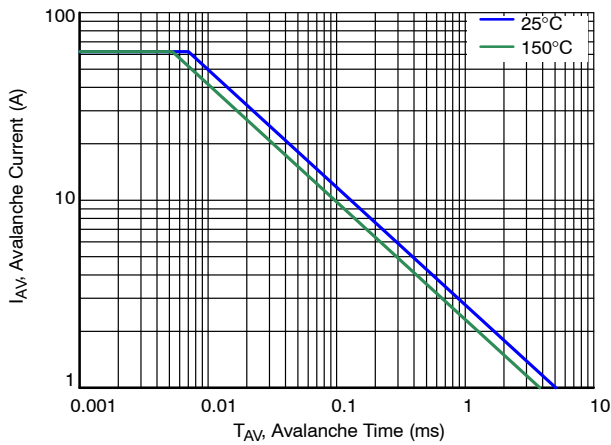


Figure 15. Avalanche Current vs Pulse Time (UIS)

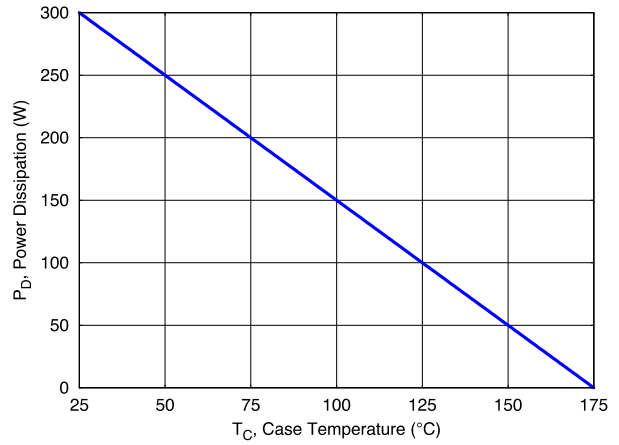


Figure 16. Maximum Power Dissipation vs Case Temperature

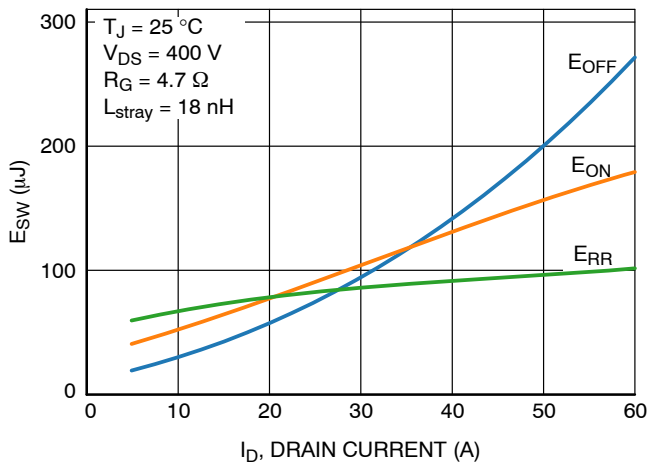


Figure 17. E_{SW} vs. I_D

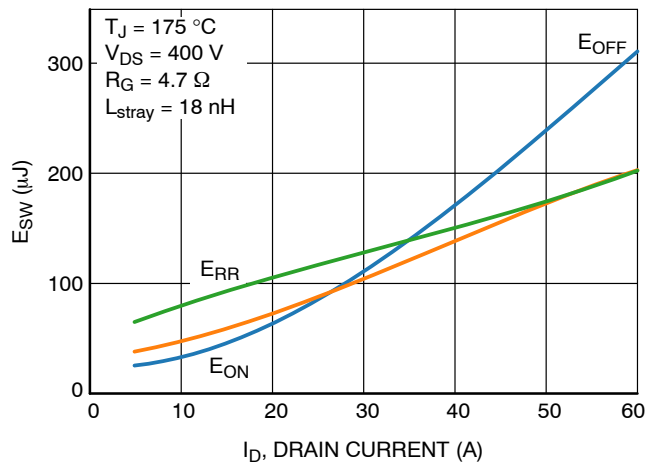


Figure 18. E_{SW} vs. I_D

TYPICAL CHARACTERISTICS

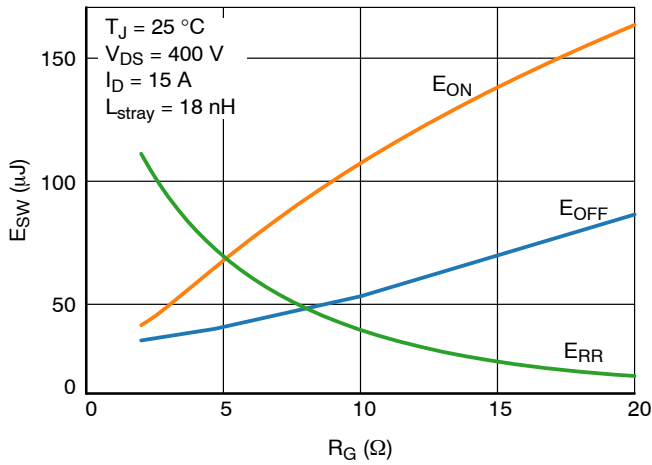


Figure 19. E_{SW} vs. R_G

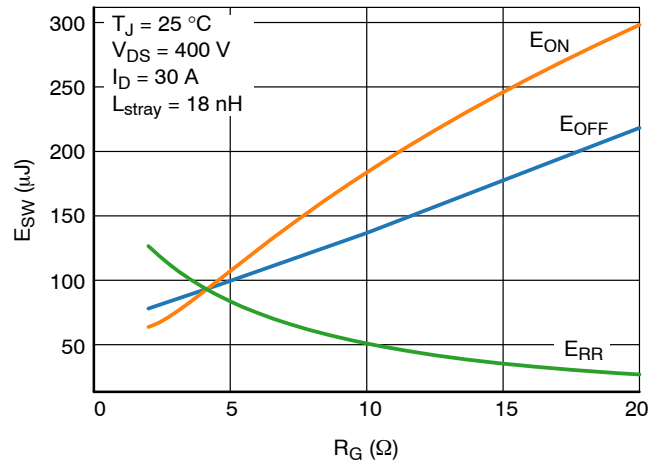


Figure 20. E_{SW} vs. R_G

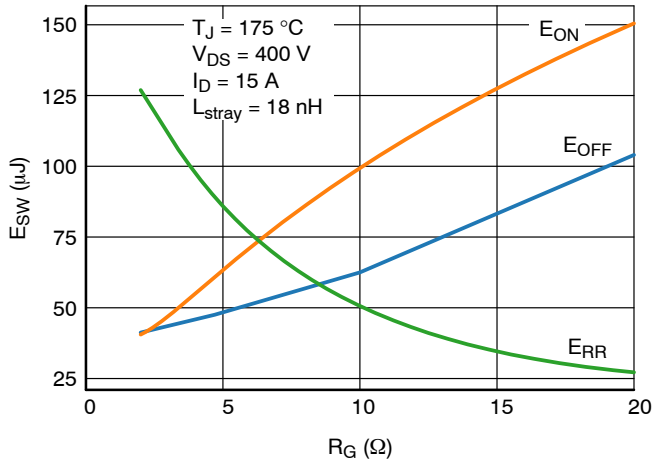


Figure 21. E_{SW} vs. R_G

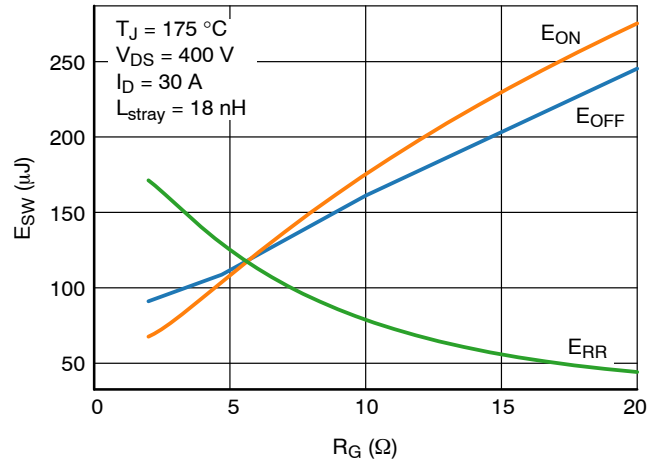


Figure 22. E_{SW} vs. R_G

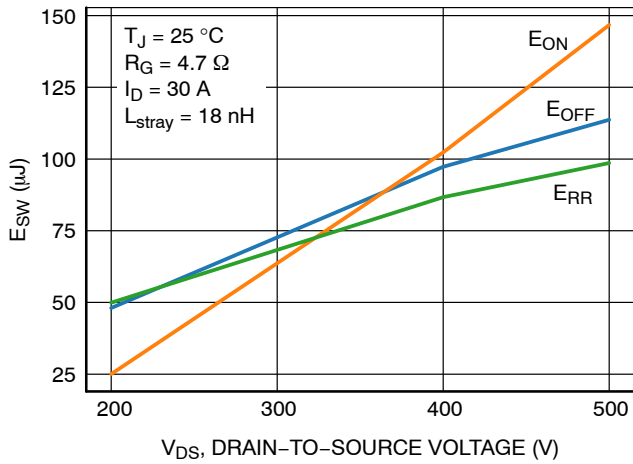


Figure 23. E_{SW} vs. V_{DS}

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TYPICAL CHARACTERISTICS

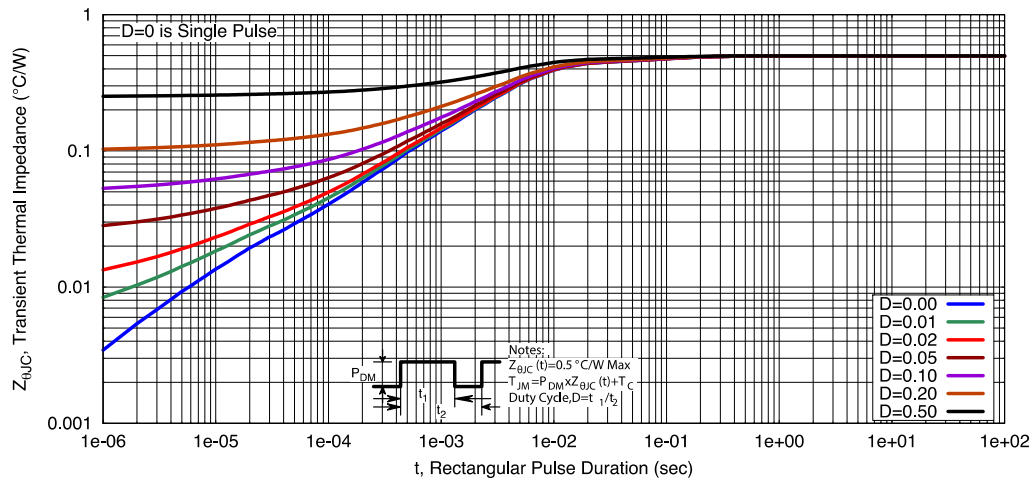
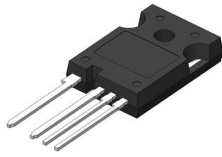


Figure 24. Thermal Response Characteristics

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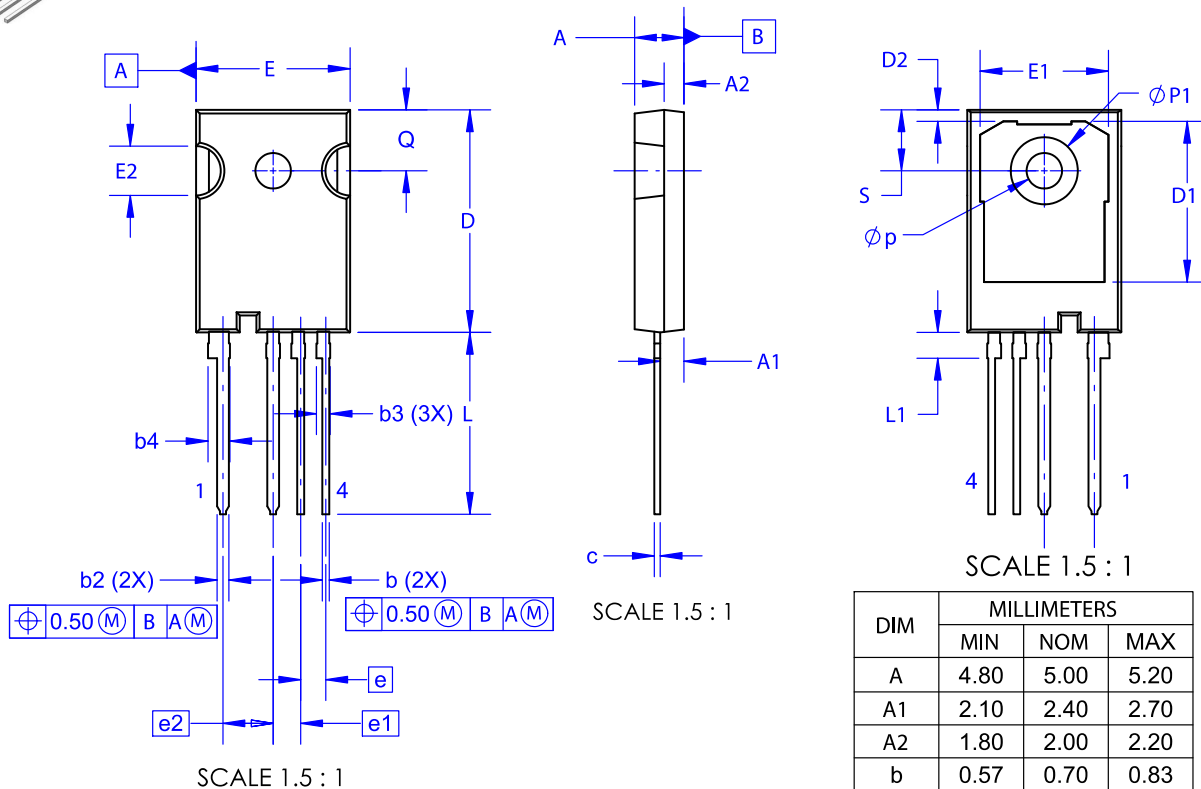
REVISION HISTORY

Revision	Description of Changes	Date
0	Initial datasheet release	7/31/2026
1	Added Gate-to-Source Transient Voltage specification.	8/3/2026



TO-247 4-LEAD, THIN LEADS
CASE 340CW
ISSUE A

DATE 16 SEP 2019



NOTES:

- A. NO INDUSTRY STANDARD APPLIES TO THIS PACKAGE.
 B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
 C. ALL DIMENSIONS ARE IN MILLIMETERS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.10	2.40	2.70
A2	1.80	2.00	2.20
b	0.57	0.70	0.83
b2	1.07	1.20	1.33
b3	1.20	1.40	1.60
b4	2.02	2.22	2.42
c	0.50	0.60	0.70
D	22.34	22.54	22.74
D1	16.00	16.30	16.50
D2	0.97	1.17	1.37
e		2.54	
e1		2.79	
e2		5.08	
E	15.40	15.60	15.80
E1	12.80	13.00	13.20
E2	4.80	5.00	5.20
L	18.12	18.42	18.72
L1	2.42	2.62	2.82
Øp	3.40	3.60	3.80
ØP1	6.60	6.80	7.00
Q	5.97	6.17	6.37
S	5.97	6.17	6.37

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